L Number	Hits	Search Text	DB	Time stamp
1	8	("111" adj plane adj substrate) with (recess or hollow or groove or (cut adj out) or hole or via)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:02
2	0	("111" adj plane) with (hollow adj substrate)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:02
3	0	("111" adj plane) with (hollow near substrate)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:02
4	3	("111" adj plane) with (hollow with substrate)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:44
5	0	(soi adj (layer or film)) with (supporting adj substrate) with (crystal adj direction)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:45
6	1	(soi adj (layer or film)) with (substrate) with (crystal adj direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:46
7	3	(soi) with (substrate) with (crystal adj direction)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 16:36
8	0	(silicon adj "on" adj insulator) with (substrate) with (crystal adj direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01
9	0	(silicon adj "on" adj insulator) with (substrate) with (direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:51
10	299	(soi) with (substrate) with (direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:52
11	8	(soi) with (substrate) with (direction) with different	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:54
12	2	(soi) with (substrate) with (orientation) with different	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:54
13	37	(soi) with (substrate) with (crystal adj orientation)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:56
14	141	crystal adj (direction or orientation) adj different	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 16:37
_			IBM TDB	

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				0004/02/01
15	3	(==2==::= ::)	USPAT;	2004/03/01
		adj different) and (soi with substrate)	US-PGPUB;	16:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	21	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/03/01
		adj different) and ((semiconductor adj	US-PGPUB;	16:55
		(layer or film)) with substrate)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
17	l 0	crystal adj direction adj soi adj layer	USPĀT;	2004/03/01
			US-PGPUB;	16:55
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
18	L 2	crystal adj direction adj substrate	USPAT;	2004/03/01
10	31	Crystal adj direction adj substrate	US-PGPUB;	16:55
			EPO; JPO;	16.55
	ì			
			DERWENT;	
			IBM_TDB	
19	1	,	USPAT;	2004/03/01
	1	soi	US-PGPUB;	17:09
	1		EPO; JPO;	, ,
			DERWENT;	
			IBM_TDB	<u> </u>
20	0	contact adj plug adj extending adj	USPAT;	2004/03/01
		through adj oxide	US-PGPUB;	17:11
		_ · · -	EPO; JPO;	
1	1		DERWENT;	
	1		IBM TDB	
21	5	contact adj plug adj oxide	USPAT;	2004/03/01
~ 1	1	consuct adj prag adj onide	US-PGPUB;	17:11
			EPO; JPO;	-''
			DERWENT;	
	1			
1 22	_	/and an /arminondurates and Ward and	IBM_TDB	1 2004/02/01
22	l o	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
		insulator)) adj (contact adj plug)	US-PGPUB;	17:12
]			EPO; JPO;	
			DERWENT;	
1	1	[, , , , , , , , , , , , , , , , , , ,	IBM_TDB	
23	1	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
		insulator)) near (contact adj plug)	US-PGPUB;	17:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
24	32	(soi or (semiconductor adj "on" adj	USPĀT;	2004/03/01
		insulator)) with (contact adj plug)	US-PGPUB;	17:17
]		EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
25	12	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
I		insulator)) with (contact adj via)	US-PGPUB;	17:18
			EPO; JPO;	
	!		DERWENT;	
			IBM TDB	
26	200	/soi or /somiconductor add "an" add	USPAT;	2004/03/01
20	290	(soi or (semiconductor adj "on" adj	US-PGPUB;	17:27
]		insulator)) with (contact adj hole)	· ·	11:41
1			EPO; JPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	2004/02/01
27	19		USPAT;	2004/03/01
		insulator)) with (contact adj opening)	US-PGPUB;	17:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	4	6229165.pn. and substrate	USPAT;	2004/03/01
			US-PGPUB;	17:32
			EPO; JPO;	
[DERWENT;	
			IBM TDB	
				

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				0004/00/01
-	17	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
		insulator)) and ((hollow or recessed) adj	US-PGPUB;	17:12
		substrate)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	514	(soi or (semiconductor adj "on" adj	USPAT;	2004/02/26
	1	insulator)) and ((hollow or recessed)	US-PGPUB;	10:48
		with substrate)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	40	(soi or (semiconductor adj "on" adj	USPAT;	2004/02/26
		insulator)) and ((cut adj out) with	US-PGPUB;	10:57
		substrate)	EPO; JPO;	
į			DERWENT;	
			IBM_TDB	
2	225	((soi or (semiconductor adj "on" adj	USPAT;	2004/02/26
		insulator)) and ((via or hole or opening)	US-PGPUB;	11:16
		adj substrate)) and 257/\$.ccls.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2071	257/347.ccls.	USPAT;	2004/02/26
			US-PGPUB;	15:17
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1_	205	257/348.ccls.	USPĀT;	2004/02/26
	203		US-PGPUB;	15:21
1			EPO; JPO;	- -
1			DERWENT;	
			IBM TDB	
1_	417	257/349.ccls.	USPAT;	2004/02/26
	11/	237/349.0013.	US-PGPUB;	15:29
			EPO; JPO;	13.23
			DERWENT;	
			IBM TDB	
	930	257/350.ccls.	USPAT;	2004/02/26
-	930	257/350.CCIS.	US-PGPUB;	15:40
			EPO; JPO;	13.40
			DERWENT;	
			IBM TDB	
	536	257/351.ccls.	USPAT;	2004/02/26
-	536	25 // 351. CCIS.	US-PGPUB;	15:50
			EPO; JPO;	15:50
1	İ		DERWENT;	
	1		IBM TDB	
	1 200	257/252 gg]g	USPAT;	2004/02/26
1 -	380	257/352.ccls.	US-PGPUB;	15:54
				13.34
			EPO; JPO;	
1	1		DERWENT;	
	1 222	257/252	IBM_TDB	2004/02/26
-	280	257/353.ccls.	USPAT;	2004/02/26
			US-PGPUB;	15:58
			EPO; JPO;	
			DERWENT;	
		257/254	IBM_TDB	2004/03/01
-	285	257/354.ccls.	USPAT;	2004/03/01
			US-PGPUB;	09:21
			EPO; JPO;	
			DERWENT;	
		6004004	IBM_TDB	2004/02/01
-	1	6084284.pn. and soi	USPAT;	2004/03/01
1			US-PGPUB;	09:26
1			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	2004/02/01
-	1	6084284.pn. and (mechanical adj support	USPAT;	2004/03/01
1		adj layer)	US-PGPUB;	09:27
			EPO; JPO;	
/			DERWENT;]
1	1		IBM TDB	

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<u> </u>	0	6084284.pn. and (silicon adj support adj	USPAT;	2004/03/01
		layer)	US-PGPUB;	09:28
		Layer,	EPO; JPO;	53.25
			DERWENT;	
			IBM TDB	1
_	1	6084284.pn. and (thick adj silicon)	USPAT;	2004/03/01
	_	•••• ••••••••••••••••••••••••••••••••	US-PGPUB;	09:27
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	6084284.pn. and (support adj layer)	USPĀT;	2004/03/01
į	_		US-PGPUB;	09:28
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
_	1	6084284.pn. and (support)	USPAT;	2004/03/01
1		• • • • • •	US-PGPUB;	10:23
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
_	280	substrate and (four adj faces)	USPAT;	2004/03/01
			US-PGPUB;	10:24
			EPO; JPO;	ļ.
			DERWENT;	
			IBM_TDB	
-	48	substrate with (four adj faces)	USPAT;	2004/03/01
			US-PGPUB;	10:33
			EPO; JPO;	1
			DERWENT;	
	_		IBM_TDB	0004/02/01
-	5	substrate with (four adj end adj faces)	USPAT;	2004/03/01
1			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
	1188	 substrate with ("111" adj plane)	IBM_TDB USPAT;	2004/03/01
_	1100	Substrate with (III adj plane)	US-PGPUB;	10:37
			EPO; JPO;	10.57
			DERWENT;	
		,	IBM TDB	
1_	160	substrate with ("111" adj plane) with	USPAT;	2004/03/01
	160	(recess or hollow or groove or (cut adj	US-PGPUB;	14:59
		out) or hole or via)	EPO; JPO;	****
		out, of hore of via,	DERWENT;	
			IBM TDB	

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